



SEMICONDUCTOR MEMORY DEVICE

D. U. to Enter
2005
08 102105

BACKGROUND OF THE INVENTION

1. Field of the Invention

The present invention relates to a Dynamic Random Access Memory (DRAM) as a semiconductor memory device and, particularly, to a DRAM for realizing data writing at a high speed.

10 2. Description of the Related Art

A DRAM is a semiconductor memory device for storing data in accordance with stored charges of capacity elements, and a memory cell normally comprises one capacitor and one transistor. In each memory cell, a control terminal (gate) 15 of the transistor is connected to a word line and a memory cell is selected by an activation voltage applied to the word line.

FIG. 5 is a circuit diagram of a partial configuration of a normal DRAM. As shown in FIG. 5, the 20 DRAM comprises a memory cell array 100a, a bit line equalizer 102, a sense amplifier 150a and a column selector 160a.